Robert M Farrell

List of Publications by Year
in descending order

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37 papers	1,725 citations	361413 20 h-index	434195 31 g-index
37 all docs	37 docs citations	37 times ranked	1549 citing authors

#	Article	IF	Citations
1	Demonstration of Nonpolarm-Plane InGaN/GaN Laser Diodes. Japanese Journal of Applied Physics, 2007, 46, L190-L191.	1.5	204
2	High internal and external quantum efficiency InGaN/GaN solar cells. Applied Physics Letters, 2011, 98, .	3.3	195
3	High luminous flux from single crystal phosphor-converted laser-based white lighting system. Optics Express, 2016, 24, A215.	3.4	153
4	4 Gbps direct modulation of 450 nm GaN laser for high-speed visible light communication. Optics Express, 2015, 23, 16232.	3.4	117
5	2 Gbit/s data transmission from an unfiltered laser-based phosphor-converted white lighting communication system. Optics Express, 2015, 23, 29779.	3.4	103
6	Continuous-wave Operation of AlGaN-cladding-free Nonpolar m-Plane InGaN/GaN Laser Diodes. Japanese Journal of Applied Physics, 2007, 46, L761.	1.5	83
7	AlGaN-Cladding Free Green Semipolar GaN Based Laser Diode with a Lasing Wavelength of 506.4 nm. Applied Physics Express, 2010, 3, 011002.	2.4	82
8	Gigabit-per-second white light-based visible light communication using near-ultraviolet laser diode and red-, green-, and blue-emitting phosphors. Optics Express, 2017, 25, 17480.	3.4	75
9	High luminous efficacy green light-emitting diodes with AlGaN cap layer. Optics Express, 2016, 24, 17868.	3.4	74
10	AlGaN-Cladding-Free Nonpolar InGaN/GaN Laser Diodes. Japanese Journal of Applied Physics, 2007, 46, L284-L286.	1.5	73
11	Effect of doping and polarization on carrier collection in InGaN quantum well solar cells. Applied Physics Letters, 2011, 98, .	3.3	68
12	Blue-Green InGaN/GaN Laser Diodes on Miscutm-Plane GaN Substrate. Applied Physics Express, 0, 2, 082102.	2.4	56
13	Effect of quantum well cap layer thickness on the microstructure and performance of InGaN/GaN solar cells. Applied Physics Letters, 2012, 100, .	3.3	53
14	Development of high performance green c-plane III-nitride light-emitting diodes. Optics Express, 2018, 26, 5591.	3.4	47
15	Surface Structured Optical Coatings with Near-Perfect Broadband and Wide-Angle Antireflective Properties. Nano Letters, 2014, 14, 5960-5964.	9.1	39
16	Nonpolar AlGaN-Cladding-Free Blue Laser Diodes with InGaN Waveguiding. Applied Physics Express, 0, 2, 071003.	2.4	37
17	Valence band states and polarized optical emission from nonpolar and semipolar IIIâ€“nitride quantum well optoelectronic devices. Japanese Journal of Applied Physics, 2014, 53, 100206.	1.5	34
18	InGaN/GaN Blue Laser Diode Grown on Semipolar (30ar31) Free-Standing GaN Substrates. Applied Physics Express, 2010, 3, 052702.	2.4	27

#	Article	IF	Citations
19	Continuous-Wave Operation of Pure Blue AlGaN-Cladding-Free Nonpolar InGaN/GaN Laser Diodes. Applied Physics Express, 2010, 3, 092103.	2.4	27
20	Dynamic characteristics of 410â€‰nm semipolar (202Â¯1Â¯) III-nitride laser diodes with a modulation bandwidth of over 5 GHz. Applied Physics Letters, 2016, 109, .	3.3	27
21	Semipolar IIIâ€“nitride light-emitting diodes with negligible efficiency droop up to âˆ¼1 W. Applied Physics Express, 2016, 9, 102102.	2.4	26
22	Observation of positive thermal power coefficient in InGaN/GaN quantum well solar cells. Applied Physics Letters, 2011, 99, 071104.	3.3	22
23	Measurement and analysis of internal loss and injection efficiency for continuous-wave blue semipolar (202Â¯1Â¯) III-nitride laser diodes with chemically assisted ion beam etched facets. Applied Physics Letters, 2016, 108, .	3.3	21
24	Using tunnel junctions to grow monolithically integrated optically pumped semipolar III-nitride yellow quantum wells on top of electrically injected blue quantum wells. Optics Express, 2017, 25, 3841.	3.4	17
25	Demonstration of low resistance ohmic contacts to p-type (202Ì„1Ì„) GaN. Semiconductor Science and Technology, 2015, 30, 075007.	2.0	12
26	Semipolar GaN-based laser diodes for Gbit/s white lighting communication: devices to systems. , 2018, , .		9
27	Semipolar III-nitride laser diodes with zinc oxide cladding. Optics Express, 2017, 25, 16922.	3.4	8
28	Blue InGaN/GaN laser diodes grown on (33$ ar 3 ar 1 $) freeâ€standing GaN substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2390-2392.	0.8	7
29	Influence of the Structure Parameters on the Relaxation of Semipolar InGaN/GaN Multi Quantum Wells. Japanese Journal of Applied Physics, 2013, 52, 08JC10.	1.5	7
30	Comparison of Polished and Dry Etched Semipolar $(11ar{2}2)$ III-Nitride Laser Facets. IEEE Photonics Technology Letters, 2013, 25, 2105-2107.	2.5	6
31	Effects of active region design on gain and carrier injection and transport of CW semipolar InGaN laser diodes. Applied Physics Express, 2016, 9, 092104.	2.4	6
32	AlGaN-Cladding-Free m-Plane InGaN/GaN Laser Diodes with p-Type AlGaN Etch Stop Layers. Applied Physics Express, 2011, 4, 092105.	2.4	4
33	Zinc oxide clad limited area epitaxy semipolar III-nitride laser diodes. Optics Express, 2018, 26, 12490.	3.4	4
34	A semipolar (10-1-3) InGaN/GaN green light emitting diode. Materials Research Society Symposia Proceedings, 2005, 892, 418.	0.1	1
35	High-speed performance of III-nitride 410 nm ridge laser diode on (202Ì„1Ì„) plane for visible light communication. , 2016, , .		1
36	Study of Temperature-Dependent Carrier Transport in a p-GaN/i-InGaN/n-GaN Solar Cell Heterostructure using Ultrafast Spectroscopy. , 2013, , .		0

#	Article	IF	Citations
37	Designing optically pumped InGaN quantum wells with long wavelength emission for a phosphor-free device with polarized white-light emission. , 2016, , .		0